



MEMC 01-0151(2960.1)
PATENT

MAY 22 2002

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of Chang Bum Kim, et al.

Serial No. 10/054,629

Filed January 22, 2002

Confirmation No. 5778

For **THERMALLY ANNEALED, LOW DEFECT DENSITY SINGLE CRYSTAL
SILICON**

May 22, 2002

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INFORMATION DISCLOSURE STATEMENT

In accordance with 37 C.F.R. 1.97 and 1.98 and MPEP 609, and in compliance with the duty of disclosure set forth in 37 C.F.R. 1.56, applicants submit copies of the references listed on the attached PTO/SB/08A for consideration by the Patent and Trademark Office in the above-entitled application and to be made of record therein.

* For the Examiner's convenience, Applicants are now submitting herewith a translation of References 50-51, 53, 55-57, 59-63, 108, and 116. Applicants make no representation as to the accuracy or completeness of these translations.

This Information Disclosure Statement is being submitted pursuant to 37 C.F.R. §1.97(b) in that Applicants believe that it is being filed prior to the mailing date of the first Office action on the merits. However, the Commissioner is hereby authorized to charge any fees incurred regarding this Information Disclosure Statement to Account No.19-1345 if an Office Action was issued prior to the date of mailing of this Statement.

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Respectfully submitted,



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of

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Application Number	10,054,629
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Confirmation Number	5778
First Named Inventor	Chang Bum Kim
Group Art Unit	1765
Examiner Name	Unknown
Attorney Docket No.	MEMC 01-0151(2960.1)

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code ² (if known)		
	1	3,997,368		Petroff et al.	12/14/1976
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		Office	Number ⁴	Kind Code ² (if known)			
42	EP	0 503 816	B1		Shin-Etsu Handotai Company Ltd.	09/16/1992	
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47	EP	0 962 557	A1		Shin-Etsu Handotai Company Ltd.	12/08/1999	
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	66	PCT	WO 98/45508		MEMC Electronic Materials Inc.	10/15/1998	

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	67	PCT	WO 98/45510		MEMC Electronic Materials Inc.	10/15/1998	
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Application Number	10,054,629
Filing Date	January 22, 2002
Confirmation Number	5778
First Named Inventor	Chang Bum Kim
Group Art Unit	1765
Examiner Name	Unknown

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